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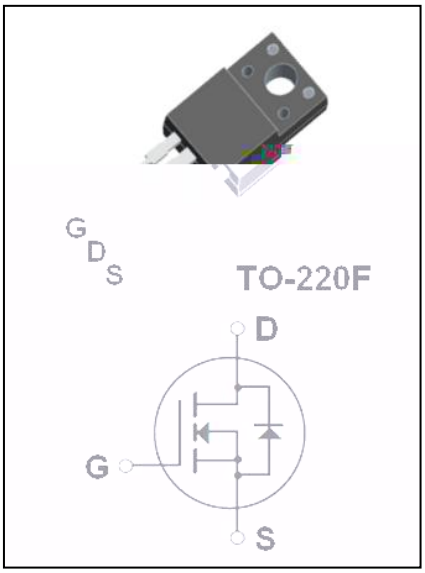

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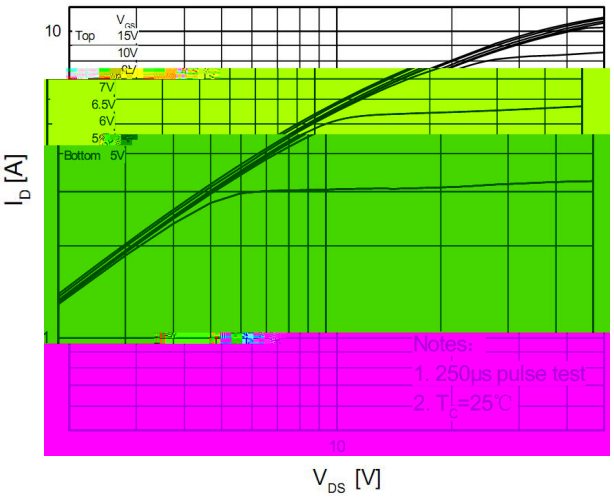
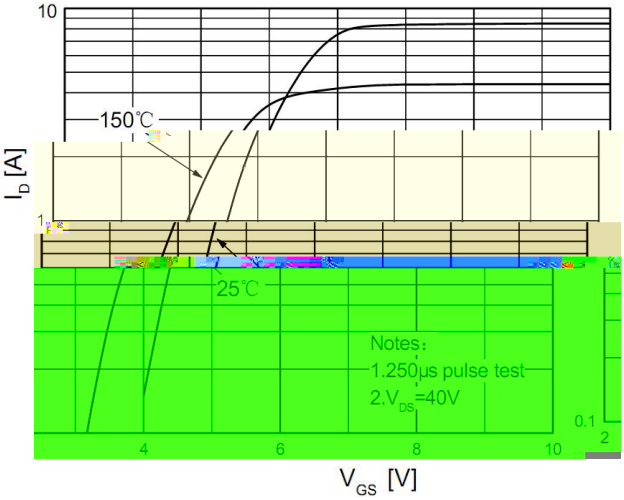
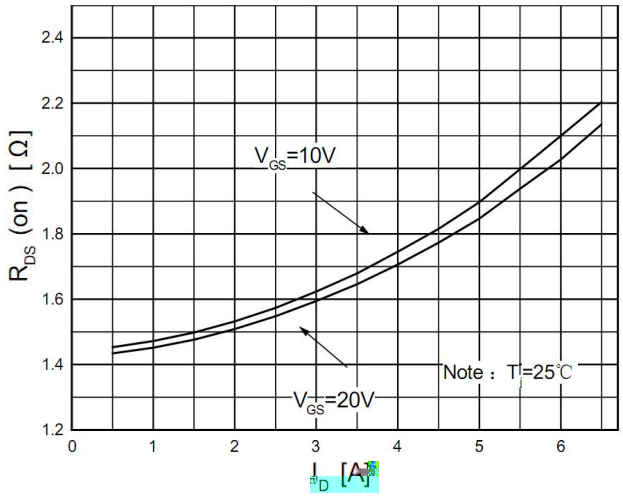
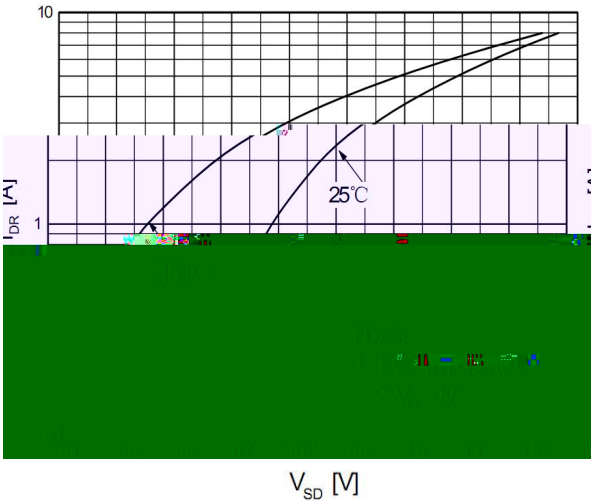
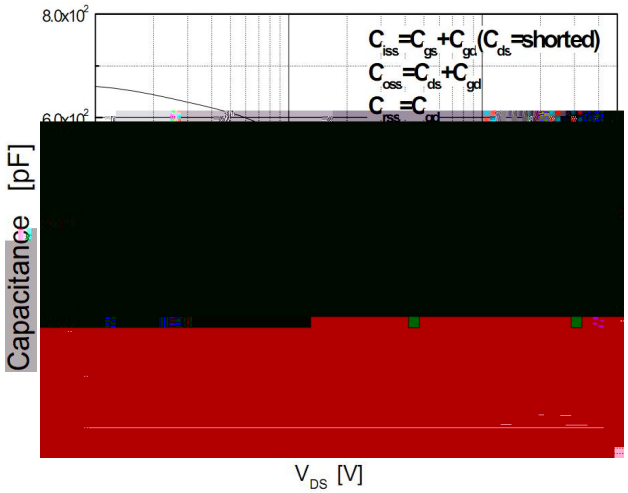
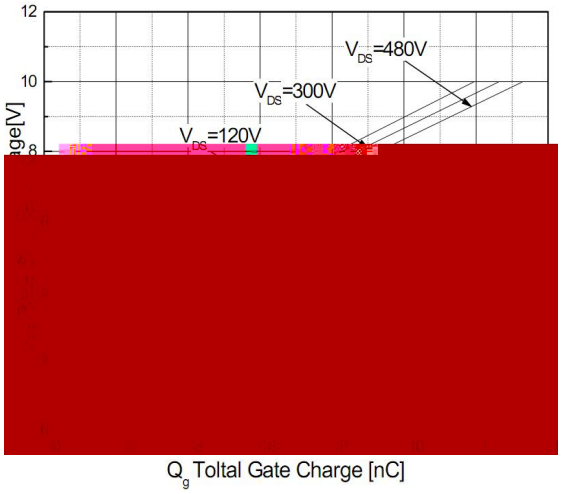

10
Top
V_{GS}
15V
10V
7V
6.5V
6V
5.5V
Bottom 5V
I_D [A]
Notes:
1. 250μs pulse test
2. T_C=25℃
V_{DS} [V]

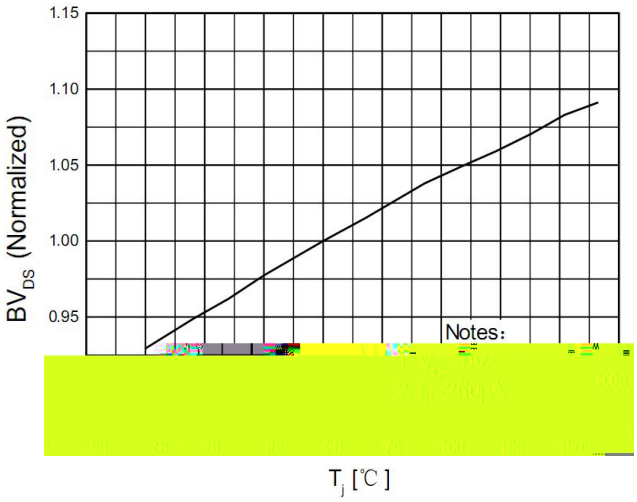

10
150℃
25℃
I_D [A]
Notes:
1.250μs pulse test
2.V_{DS}=40V
4
6
8
10
0.1
V_{GS} [V]

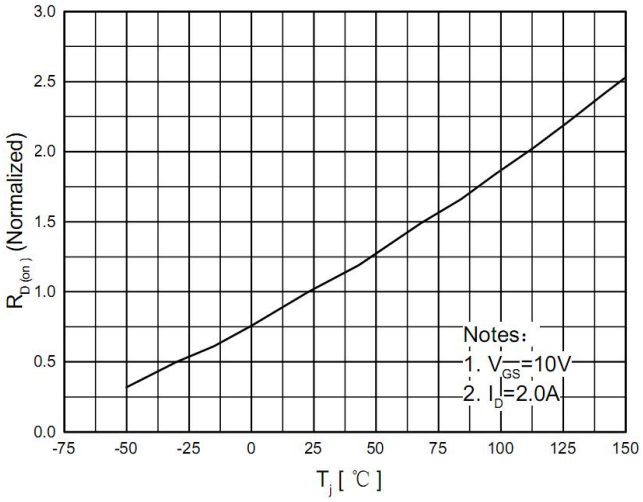

2.4
2.2
2.0
1.8
1.6
1.4
1.2
R_{DS} (on) [Ω]
V_{GS}=10V
V_{GS}=20V
Note：T_J=25℃
0
1
2
3
4
5
6
I_D [A]

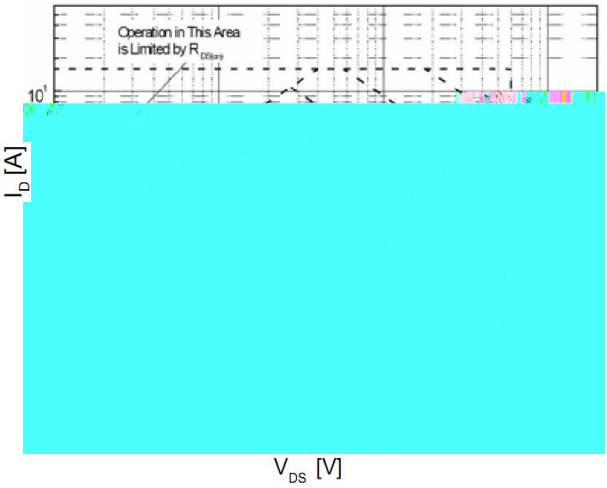

10
1
I_{DR} [A]
25℃
V_{SD} [V]

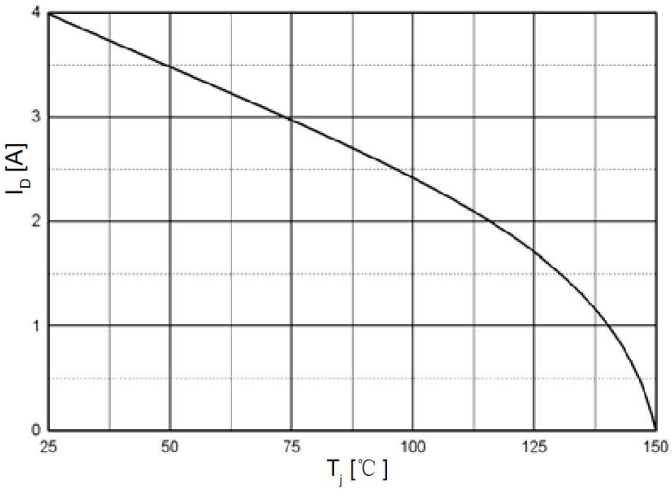

8.0x10²
6.0x10²
C_{iss}=C_{gs}+C_{gd} (C_{ds}=shorted)
C_{oss}=C_{ds}+C_{gd}
C_{rss}=C_{gd}
Capacitance [pF]
V_{DS} [V]

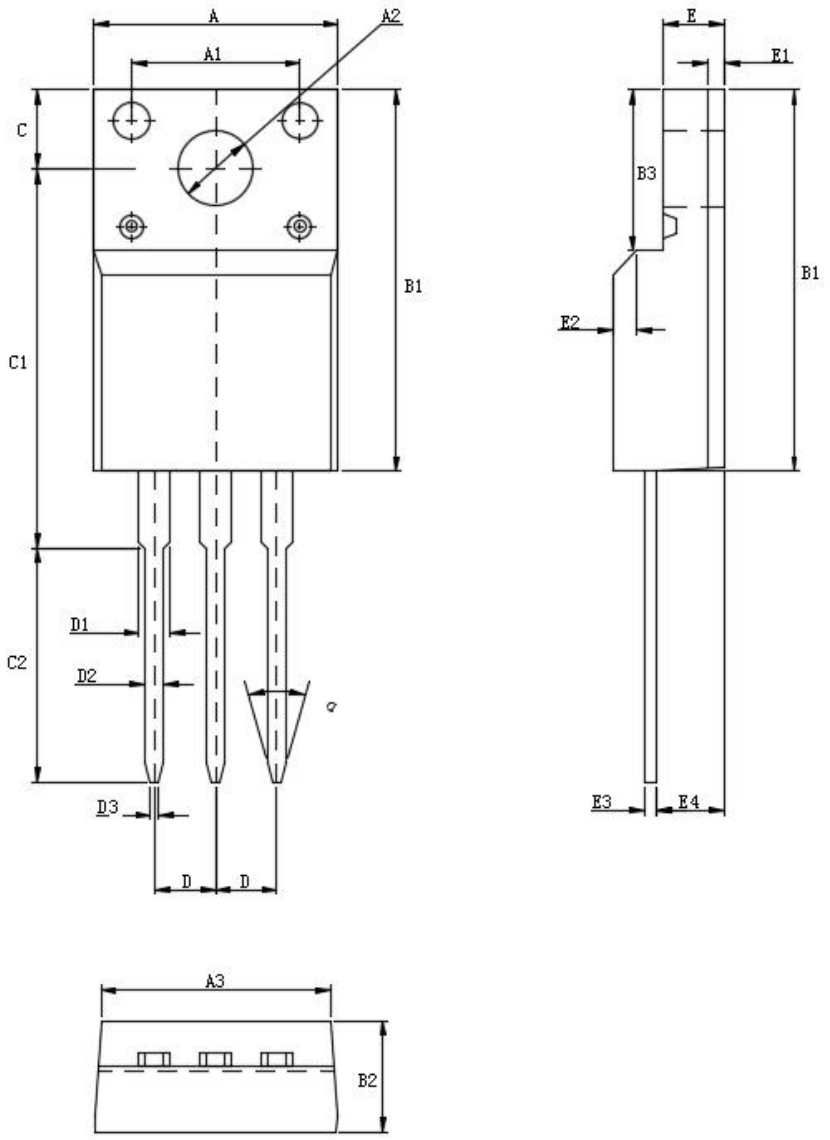

12
10
8
V_{DS}=480V
V_{DS}=300V
V_{DS}=120V
Q_g Toltal Gate Charge [nC]


1.15
1.10
1.05
1.00
0.95
BVDS (Normalized)
Notes:
Tj [℃]


3.0
2.5
2.0
1.5
1.0
0.5
0.0
RD(on) (Normalized)
Notes:
1. VGS=10V
2. ID=2.0A
-75
-50
-25
0
25
50
75
100
125
150
Tj [℃]


Operation in This Area
is Limited by RDS(on)
10¹
ID [A]
VDS [V]


4
3
2
1
0
ID [A]
25
50
75
100
125
150
Tj [℃]


A
A2
A1
C
B1
C1
D1
C2
D2
α
D3
D
D
E
E1
B3
B1
E2
E3
E4
A3
B2